

Schottky barrier diode

LRB550V-30T1G

●Applications

General rectification

●Features

- 1) Small surface mounting type.
- 2) Low V_F , Low I_R
- 3) High reliability.
- 3) We declare that the material of product compliance with RoHS requirements.

●Construction

Silicon epitaxial planar

●Device Marking and Ordering Information

Device	Marking	Shipping
LRB550V-30T1G	SD	3000/Tape&Reel
LRB550V-30T3G	SD	10000/Tape&Reel

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

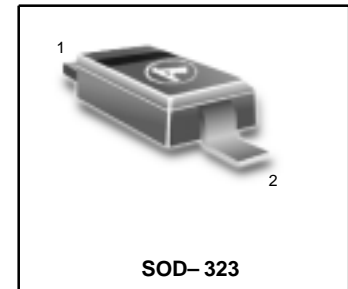
Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	30	V
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_o	0.5	A
Forward current surge peak	I_{FSM}	2	A
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +150	$^\circ\text{C}$

* 60Hz for 1 ϕ

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	-	-	0.39	V	$I_F=100\text{mA}$
	V_{F2}	-	-	0.60	V	$I_F=700\text{mA}$
Reverse current	I_R	-	-	30	μA	$V_R=10\text{V}$

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● Electrical characteristic curves (Ta = 25°C)

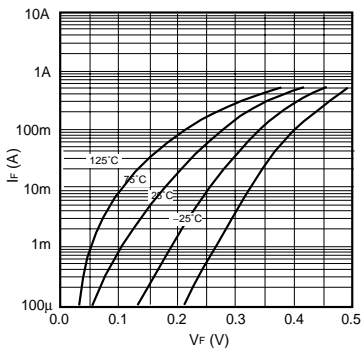


Fig.1 Forward characteristics

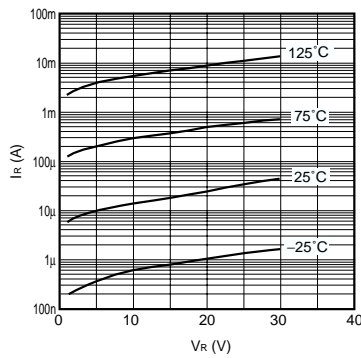


Fig.2 Reverse characteristics

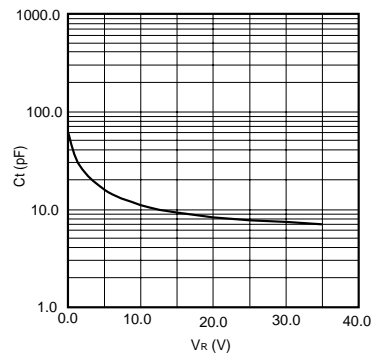
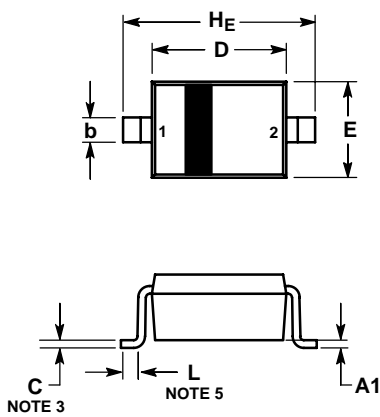


Fig.3 Capacitance between terminals characteristics

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SOD-323


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURED FROM END OF RADIUS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08		0.003			
HE	2.30	2.50	2.70	0.090	0.098	0.105

SOLDERING FOOTPRINT*
